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With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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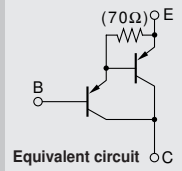
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Darlington

2SB1647



Silicon PNP Epitaxial Planar Transistor (Complement to type 2SD2560)

Application : Audio, Series Regulator and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{CB0}	-150	V
V _{CE0}	-150	V
V _{EB0}	-5	V
I _C	-15	A
I _B	-1	A
P _C	130(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

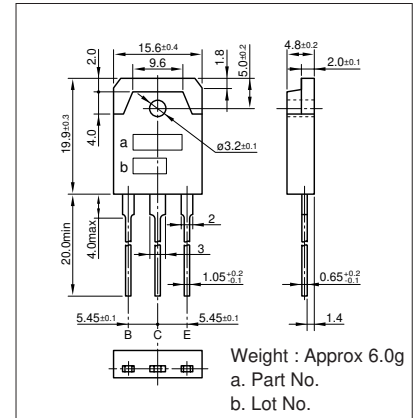
Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =-150V	-100max	μA
I _{EB0}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _C =-30mA	-150min	V
h _{FE}	V _{CE} =-4V, I _C =-10A	5000min*	
V _{CE(sat)}	I _C =-10A, I _B =-10mA	-2.5max	V
V _{BE(sat)}	I _C =-10A, I _B =-10mA	-3.0max	V
f _T	V _{CE} =-12V, I _E =2A	45typ	MHz
C _{OB}	V _{CB} =-10V, f=1MHz	320typ	pF

*h_{FE} Rank O(5000to12000), P(6500to20000), Y(15000to30000)

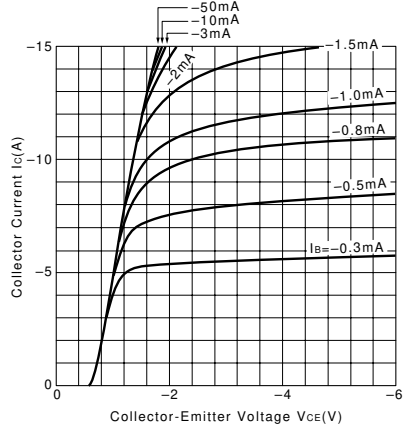
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-40	4	10	-10	5	-10	10	0.7typ	1.6typ	1.1typ

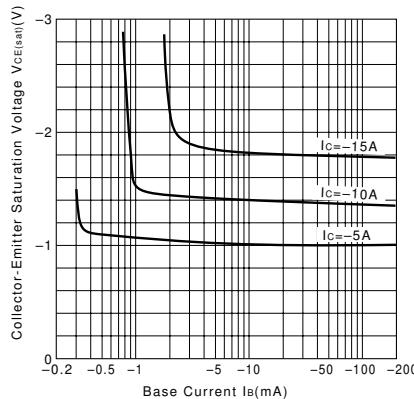
External Dimensions MT-100(TO3P)



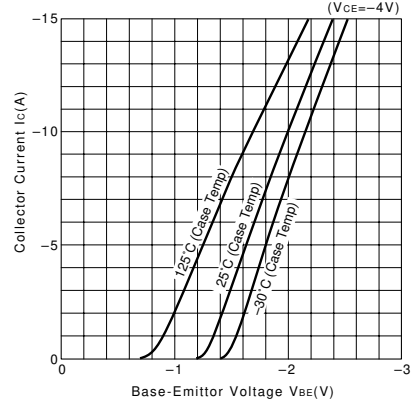
I_C-V_{CE} Characteristics (Typical)



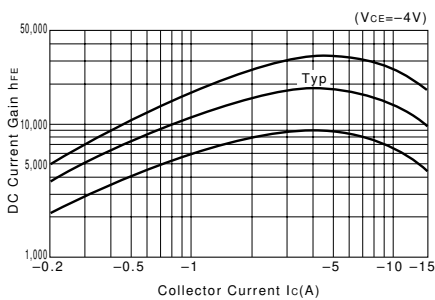
V_{CE(sat)}-I_B Characteristics (Typical)



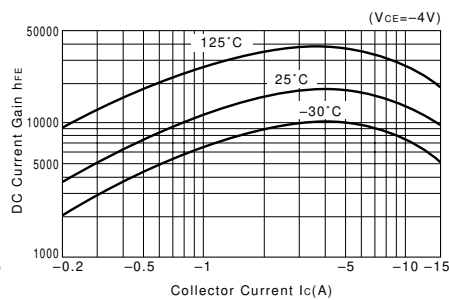
I_C-V_{BE} Temperature Characteristics (Typical)



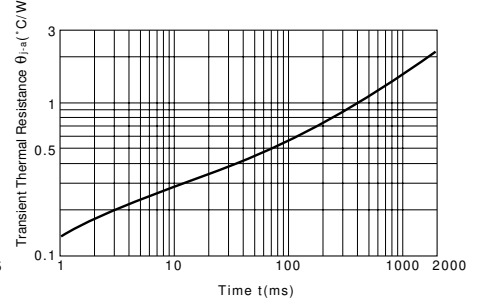
h_{FE}-I_C Characteristics (Typical)



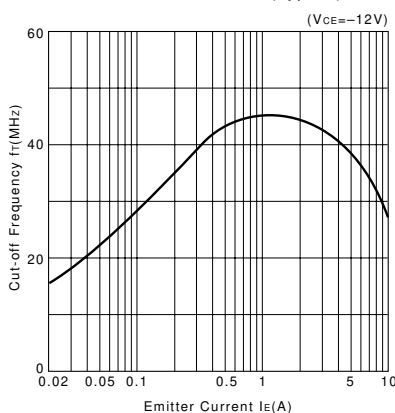
h_{FE}-I_C Temperature Characteristics (Typical)



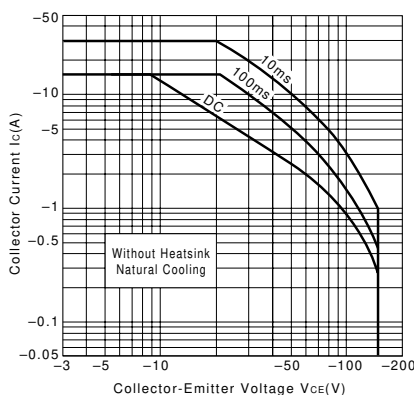
θ_{J-a}-t Characteristics



f_T-I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C-T_a Derating

